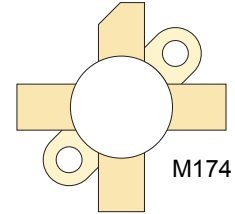



RF POWER VERTICAL MOSFET

The VRF151 is a gold-metallized silicon n-channel RF power transistor designed for broadband commercial and military applications requiring high power and gain without compromising reliability, ruggedness, or inter-modulation distortion.



FEATURES

- Improved Ruggedness $V_{(BR)DSS} = 170V$
- 150W with 22dB Typical Gain @ 30MHz, 50V
- 150W with 14dB Typical Gain @ 175MHz, 50V
- Excellent Stability & Low IMD
- Common Source Configuration
- Available in Matched Pairs
- 70:1 Load VSWR Capability at Specified Operating Conditions
- Nitride Passivated
- Refractory Gold Metallization
- High Voltage Replacement for MRF151
- RoHS Compliant 

Maximum Ratings

All Ratings: $T_c = 25^\circ C$ unless otherwise specified

Symbol	Parameter	VRF151(MP)	Unit
V_{DSS}	Drain-Source Voltage	170	V
I_D	Continuous Drain Current @ $T_c = 25^\circ C$	16	A
V_{GS}	Gate-Source Voltage	± 40	V
P_D	Total Device dissipation @ $T_c = 25^\circ C$	300	W
T_{STG}	Storage Temperature Range	-65 to 150	°C
T_J	Operating Junction Temperature	200	

Static Electrical Characteristics

Symbol	Parameter	Min	Typ	Max	Unit
$V_{(BR)DSS}$	Drain-Source Breakdown Voltage ($V_{GS} = 0V, I_D = 100mA$)	170	180		V
$V_{DS(ON)}$	On State Drain Voltage ($I_{D(ON)} = 10A, V_{GS} = 10V$)		2.0	3.0	
I_{DSS}	Zero Gate Voltage Drain Current ($V_{DS} = 100V, V_{GS} = 0V$)			1	mA
I_{GSS}	Gate-Source Leakage Current ($V_{GS} = \pm 20V, V_{DS} = 0V$)			1.0	μA
g_{fs}	Forward Transconductance ($V_{DS} = 10V, I_D = 5A$)	5.0			mhos
$V_{GS(TH)}$	Gate Threshold Voltage ($V_{DS} = 10V, I_D = 100mA$)	2.9	3.6	4.4	V

Thermal Characteristics

Symbol	Characteristic	Min	Typ	Max	Unit
$R_{\theta JC}$	Junction to Case Thermal Resistance			0.60	°C/W

 **CAUTION:** These Devices are Sensitive to Electrostatic Discharge. Proper Handling Procedures Should Be Followed.

Dynamic Characteristics

VRF151(MP)

Symbol	Parameter	Test Conditions	Min	Typ	Max	Unit
C_{iss}	Input Capacitance	$V_{GS} = 0V$ $V_{DS} = 150V$ $f = 1MHz$		375		pF
C_{oss}	Output Capacitance			200		
C_{rss}	Reverse Transfer Capacitance			12		

Functional Characteristics

Symbol	Parameter	Min	Typ	Max	Unit
G_{PS}	$f_1 = 30MHz, f_2 = 30.001MHz, V_{DD} = 50V, I_{DQ} = 250mA, P_{out} = 150W_{PEP}^1$	18	22		dB
G_{PS}	$f = 175MHz, V_{DD} = 50V, I_{DQ} = 250mA, P_{out} = 150W$		14		
η_D	$f_1 = 30MHz, f_2 = 30.001MHz, V_{DD} = 50V, I_{DQ} = 250mA, P_{out} = 150W_{PEP}^1$		50		%
IMD _(d3)	$f_1 = 30MHz, f_2 = 30.001MHz, V_{DD} = 50V, I_{DQ} = 250mA, P_{out} = 150W_{PEP}^1$		-30		dBc
ψ	$f_1 = 50MHz, V_{DD} = 50V, I_{DQ} = 250mA, P_{out} = 150W$ CW 70:1 VSWR - All Phase Angles, 0.2mSec X 20% Duty Factor	No Degradation in Output Power			

1. To MIL-STD-1311 Version A, test method 2204B, Two Tone, Reference Each Tone

Microsemi reserves the right to change, without notice, the specifications and information contained herein.

Typical Performance Curves

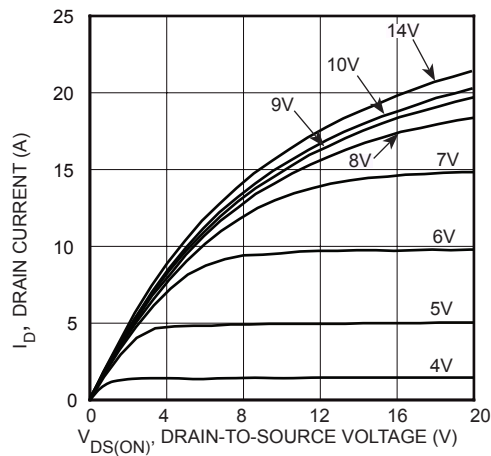


FIGURE 1, Output Characteristics

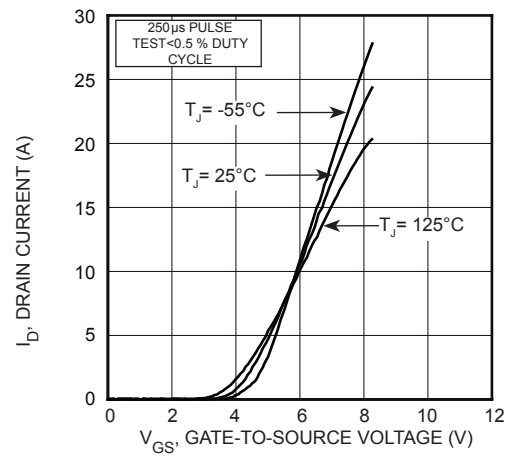


FIGURE 2, Transfer Characteristics

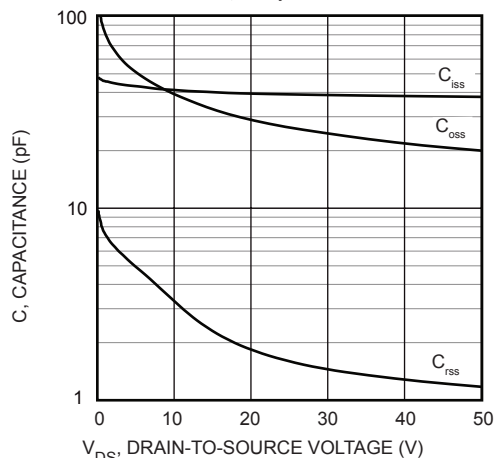


FIGURE 3, Capacitance vs Drain-to-Source Voltage

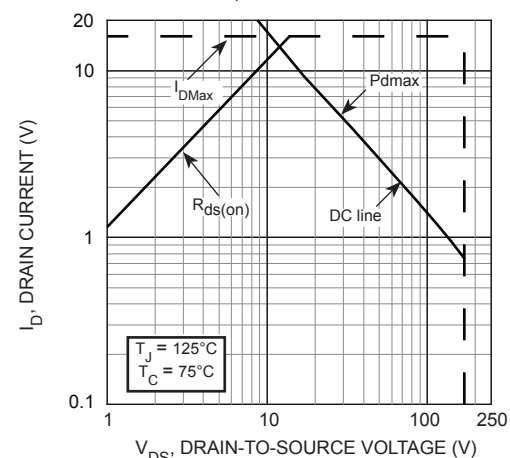


FIGURE 4, Forward Safe Operating Area

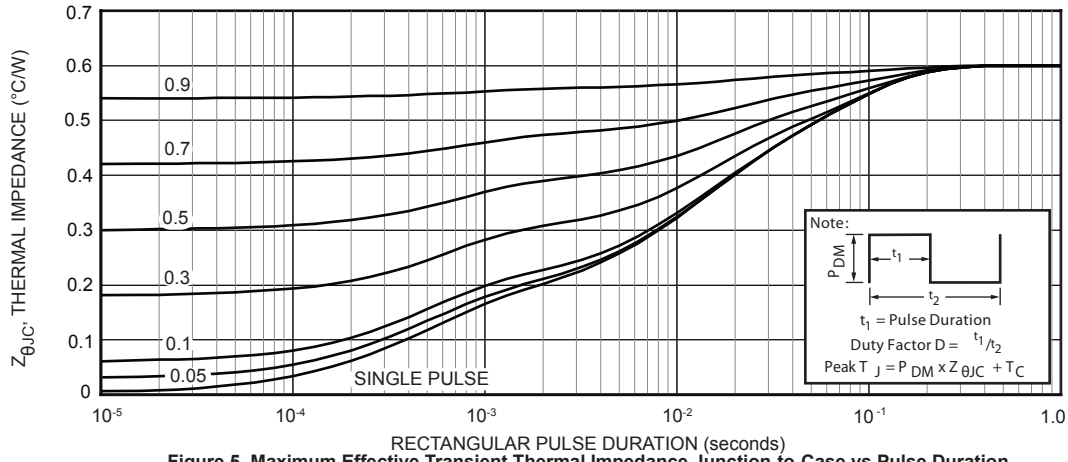


Figure 5. Maximum Effective Transient Thermal Impedance Junction-to-Case vs Pulse Duration

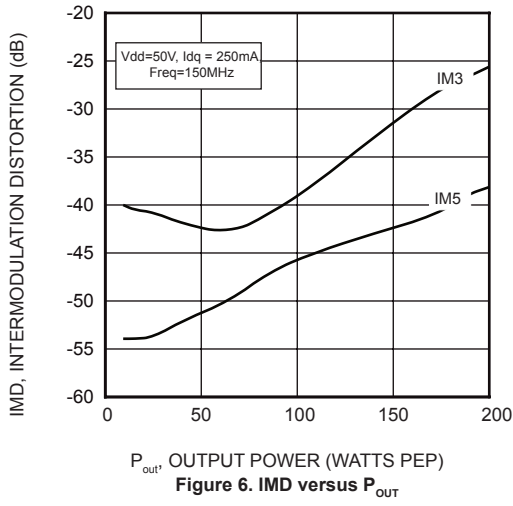


Figure 6. IMD versus P_{OUT}

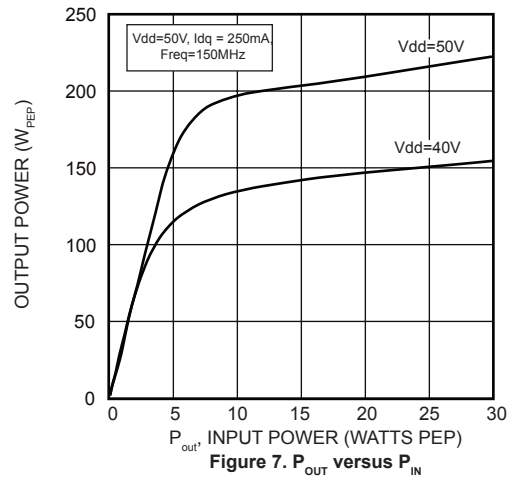
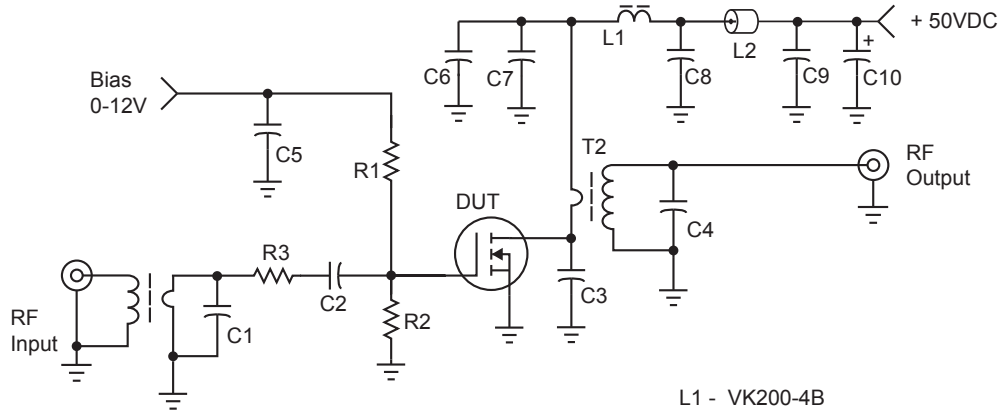


Figure 7. P_{OUT} versus P_{IN}

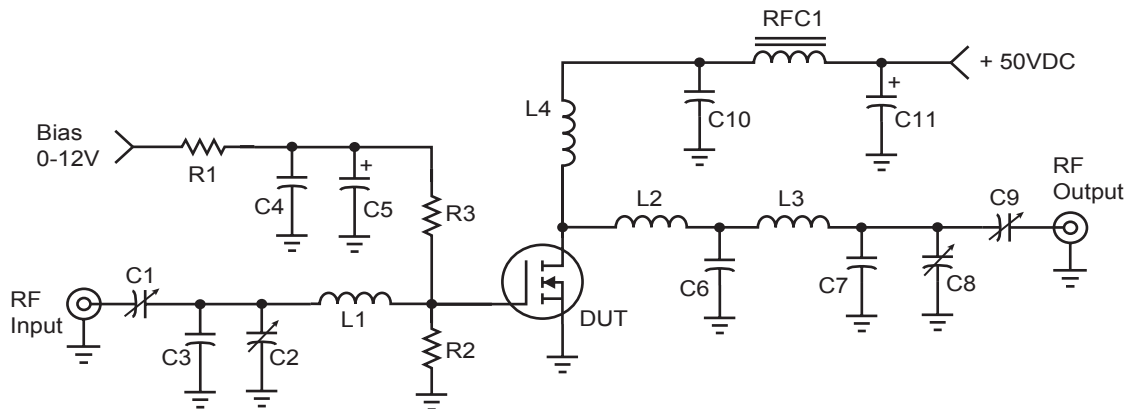
30 MHz test Circuit



- C1 -- 470 pF Dipped Mica
- C2, C5, C6 - C9 -- 0.1uF SMT
- C3 -- 200pF ATC 700C
- C4 -- 15pF, ATC 700C
- C10 -- 10uF, 100V Electrolytic

- L1 - VK200-4B
- L2 -- 2 Ferrite beads, 2.0 uH
- R1, R2 -- 51 Ω , 1 W Carbon
- R3 -- 3.3 Ω , 1 W Carbon
- T1 -- 9:1 Transformer
- T2 -- 1:9 Transformer

175 MHz test Circuit



- C1, C2, C8 -- Arco 463 or equivalent
- C3 -- 25pF, Unelco
- C4 -- 0.1uF, Ceramic
- C5 -- 1.0 uF, 15 WV Tantalum
- C6 -- 250pF, Unelco J101
- C7 -- 25pF, Unelco J101
- C9 -- Arco 262 or equivalent
- C10 -- 0.05uF, Ceramic
- C11 -- 15uF, 60WV Electrolytic

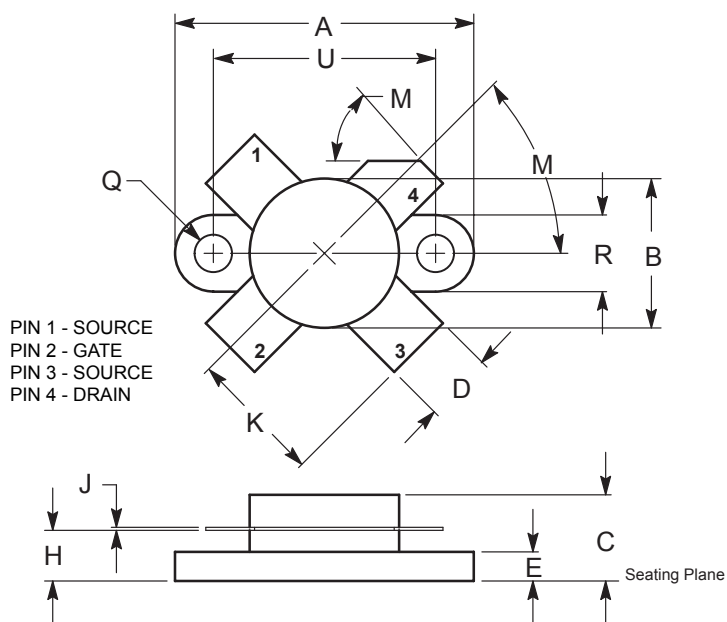
- L1 -- 3/4", #18 into Hairpin
- L2 -- Printed Line, 0.200" W x 0.500" L
- L3 -- 1", #16 into Hairpin approx 16nH
- L4 -- 2 turns #16, 5/16" ID
- RFC1 - VK200-4B
- R1 -- 150 Ω , 1/2W Carbon
- R2 -- 10k Ω , 1/2W Carbon
- R3 -- 120 Ω , 1/2W Carbon

Adding MP at the end of P/N specifies a matched pair where $V_{GS(TH)}$ is matched between the two parts. V_{TH} values are marked on the devices per the following table.

Code	Vth Range	Code 2	Vth Range
A	2.900 - 2.975	M	3.650 - 3.725
B	2.975 - 3.050	N	3.725 - 3.800
C	3.050 - 3.125	P	3.800 - 3.875
D	3.125 - 3.200	R	3.875 - 3.950
E	3.200 - 3.275	S	3.950 - 4.025
F	3.275 - 3.350	T	4.025 - 4.100
G	3.350 - 3.425	W	4.100 - 4.175
H	3.425 - 3.500	X	4.175 - 4.250
J	3.500 - 3.575	Y	4.250 - 4.325
K	3.575 - 3.650	Z	4.325 - 4.400

V_{TH} values are based on Microsemi measurements at datasheet conditions with an accuracy of 1.0%.

.5" SOE Package Outline
All Dimensions are $\pm .005$



DIM	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	0.096	0.990	24.39	25.14
B	0.465	0.510	11.82	12.95
C	0.229	0.275	5.82	6.98
D	0.216	0.235	5.49	5.96
E	0.084	0.110	2.14	2.79
H	0.144	0.178	3.66	4.52
J	0.003	0.007	0.08	0.17
K	0.435		11.0	
M	45° NOM		45° NOM	
Q	0.115	0.130	2.93	3.30
R	0.246	0.255	6.25	6.47
U	0.720	0.730	18.29	18.54